

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SA673, 2SA673A

Silicon PNP Epitaxial

RENESAS

ADE-208-125 (Z)

1st. Edition

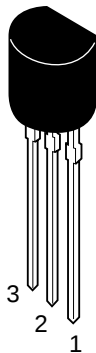
Mar. 2001

Application

- Low frequency amplifier
- Complementary pair with 2SC1213 and 2SC1213A

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA673, 2SA673A

Absolute Maximum Ratings (Ta = 25°C)

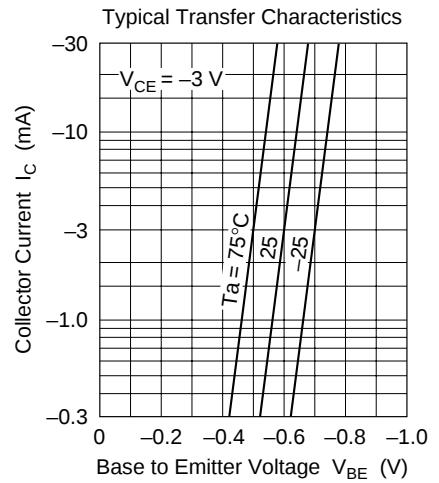
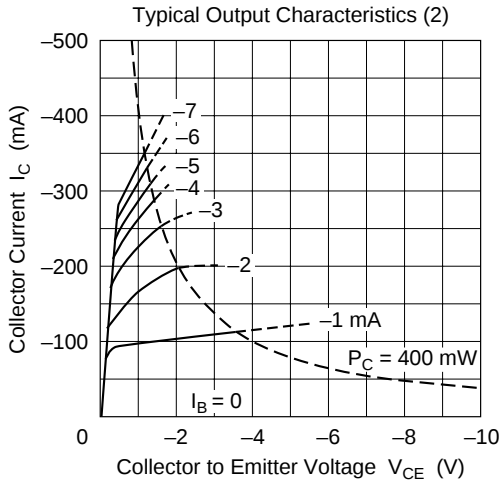
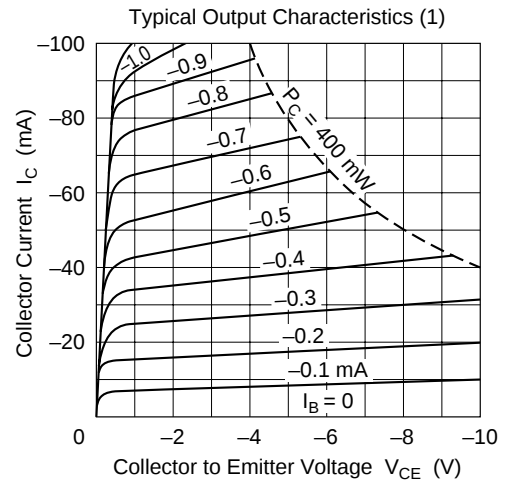
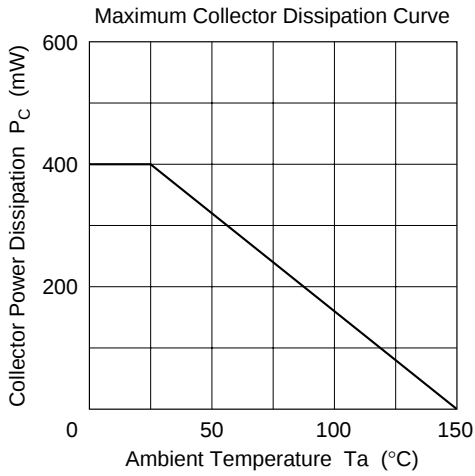
Item	Symbol	2SA673	2SA673A	Unit
Collector to base voltage	V _{CBO}	−35	−50	V
Collector to emitter voltage	V _{CEO}	−35	−50	V
Emitter to base voltage	V _{EBO}	−4	−4	V
Collector current	I _C	−500	−500	mA
Collector power dissipation	P _C	400	400	mW
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	−55 to +150	−55 to +150	°C

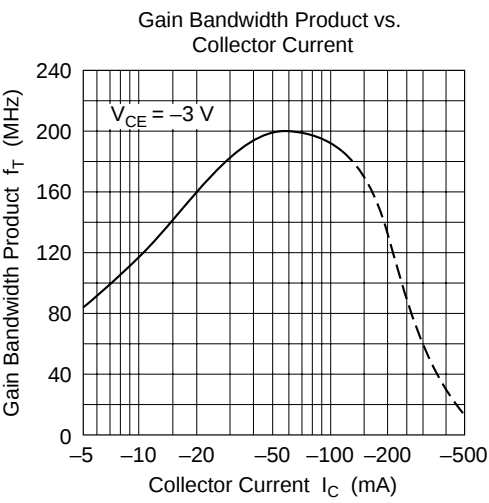
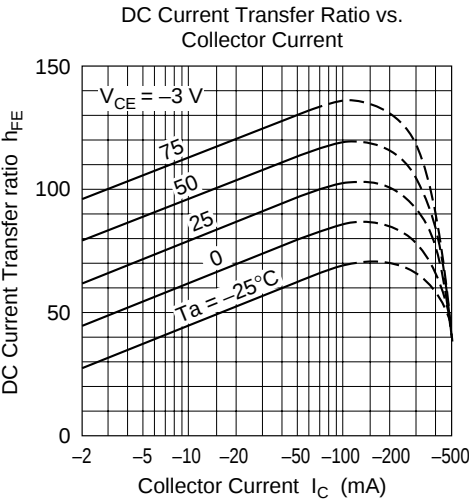
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SA673			2SA673A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	V _{(BR)CBO}	−35	—	—	−50	—	—	V	I _C = −10 μA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	−35	—	—	−50	—	—	V	I _C = −1 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	−4	—	—	−4	—	—	V	I _E = −10 μA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	−0.5	—	—	−0.5	μA	V _{CB} = −20 V, I _E = 0
Collector to emitter saturation voltage	V _{CE(sat)}	—	−0.2	−0.6	—	−0.2	−0.6	V	I _C = −150 mA, I _B = −15 mA* ²
DC current trnsfer ratio	h _{FE} * ¹	60	—	320	60	—	320		V _{CE} = −3 V, I _C = −10 mA
DC current trnsfer ratio	h _{FE}	10	—	—	10	—	—		V _{CE} = −3 V, I _C = −500 mA* ²
Base to emitter voltage	V _{BE}	—	−0.64	—	—	−0.64	—	V	V _{CE} = −3 V, I _C = −10 mA

Notes: 1. The 2SA673 and 2SA673A are grouped by h_{FE} as follows.
2. Pulse test

B	C	D
60 to 120	100 to 200	160 to 320

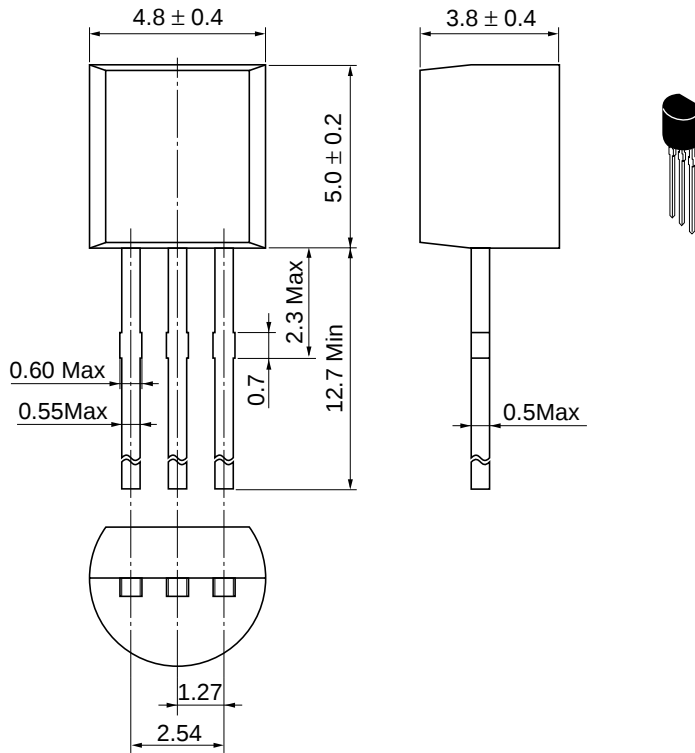




Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

Cautions

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